



ZXMN6A09K

Product Summary

BV _{DSS}	Max R _{DS(on)}	Max I _D T _A = +25°C (Note 4)
60V	40mΩ @ V _{GS} = 10V	7.7A
000	$60m\Omega @ V_{GS} = 4.5V$	6.3A

Description and Applications

This MOSFET is designed to minimize the on-state resistance $(R_{DS(on)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- DC-DC Converters
- Power Management Functions
- Disconnect Switches
- Motor Control

Features and Benefits

- Low On-Resistance
- Fast Switching Speed
- Low Gate Drive
- Lead-Free Finish; RoHS Compliant (Note 1)
- Halogen and Antimony Free. "Green" Device (Note 2 & 3)

60V N-CHANNEL ENHANCEMENT MODE MOSFET

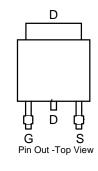
Qualified to AEC-Q101 Standards for High Reliability

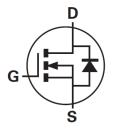
Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish. Solderable per MIL-STD-202, Method 208 3
- Weight: 0.33 grams (Approximate)



Top View





Equivalent Circuit

Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN6A09KTC	ZXMN6A09	13	16	2,500

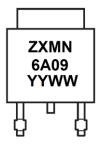
Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



ZXMN6A09 = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 10 = 2010) WW = Week (01 - 53)



Maximum Ratings (@T_A = +25°C unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage			V _{DSS}	60	V
Gate-Source Voltage		V _{GS}	±20	V	
		(Note 6)		11.8	
Continuous Drain Current	$V_{GS} = 10V$	$T_{A} = +70^{\circ}C$ (Note 6)	ID	9.6	A
		(Note 5)		7.7	
Pulsed Drain Current (Note 7		(Note 7)	I _{DM}	43	А
Continuous Source Current (Body Diode) (Note 6)		(Note 6)	ls	10.8	А
Pulsed Source Current (Body Diode) (Note 7)		I _{SM}	43	А	

Thermal Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
	(Note 5)		4.3 34.4		
Power Dissipation Linear Derating Factor	(Note 6)	P _D	10.1 80.8	W mW/°C	
	(Note 8)		2.15 17.2		
	(Note 5)		29		
Thermal Resistance, Junction to Ambient	(Note 6)	R ₀ JA	12.3	2011	
	(Note 8)		58.1	°C/W	
Thermal Resistance, Junction to Lead	(Note 9)	R _{θJL}	1.04		
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to 150	°C	

Notes: 5. For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

6. For a device surface mounted on FR4 PCB measured at t \leq 10 sec.

7. Repetitive rating 50mm x 50mm x 1.6mm FR4 PCB, D = 0.02 and pulse width 300 µs. The pulse current is limited by the maximum junction temperature.

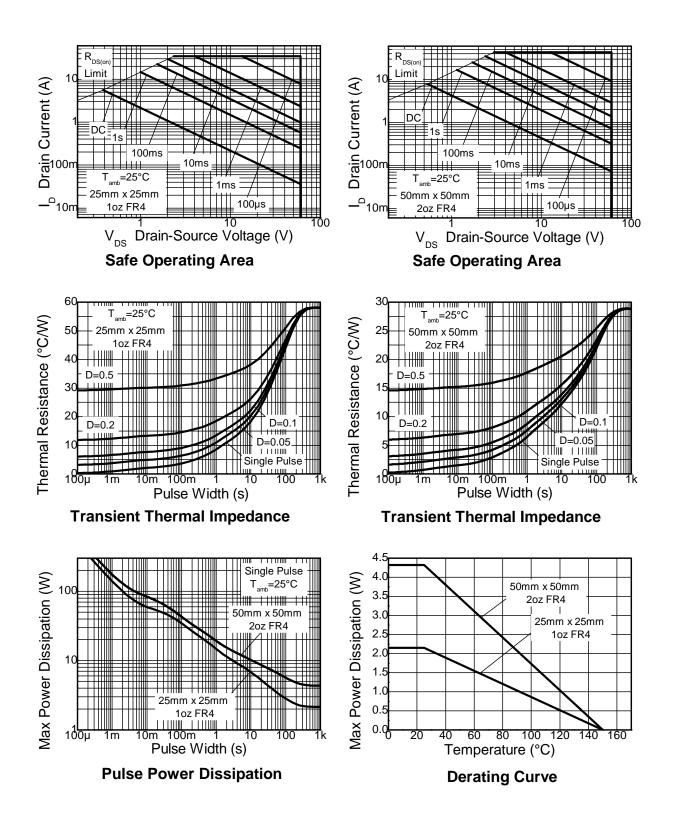
8. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is

measured when operating in a steady-state condition.

9. Thermal resistance from junction to solder-point (at the end of the drain lead).



Thermal Characteristics





Electrical Characteristics (@T_A = +25°C unless otherwise specified.)

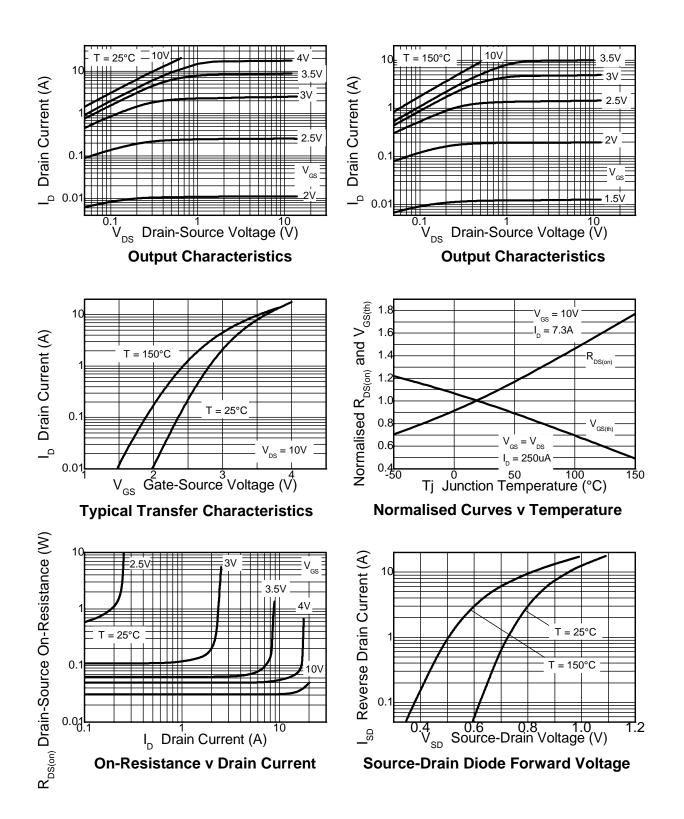
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS						÷	
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$I_D = 250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μA	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(th)}	1.0	_	3.0	V	$I_D = 250\mu A$, $V_{DS} = V_{GS}$	
Statia Drain Source On Begistenes (Note 10)	P			40	mΩ	V _{GS} = 10V, I _D = 7.3A	
Static Drain-Source On-Resistance (Note 10)	R _{DS (ON)}		_	60	11122	V _{GS} = 4.5V, I _D = 5.6A	
Forward Transconductance (Notes 10 & 11)	g fs	_	15	_	S	V _{DS} = 15V, I _D = 7.3A	
Diode Forward Voltage (Note 10)	V _{SD}		0.85	0.95	V	I _S = 6.6A, V _{GS} = 0V, T _J = +25°C	
Reverse Recovery Time (Note 11)	t _{rr}		25.6	_	ns	I _S = 3A, di/dt = 100A/μs	
Reverse Recovery Charge (Note 11)	Qrr	_	26.0	_	nC	T _J = +25°C	
DYNAMIC CHARACTERISTICS (Note 11)						÷	
Input Capacitance	Ciss	_	1426	_	pF		
Output Capacitance	Coss	_	134	_	pF	$V_{DS} = 30V, V_{GS} = 0V$ - f = 1MHz	
Reverse Transfer Capacitance	Crss	_	64	_	pF		
Total Gate Charge (Note 12)	Qq	_	15	_	nC	V _{GS} = 4.5V, V _{DS} = 30V, I _D = 5.6A	
Total Gate Charge (Note 12)	Qq	_	29	_	nC	$V_{GS} = 10V, V_{DS} = 30V$ $-I_D = 7.3A$	
Gate-Source Charge (Note 12)	Q _{gs}		7.0	—	nC		
Gate-Drain Charge (Note 12)	Q _{gd}		4.7		nC		
Turn-On Delay Time (Note 12)	t _{D(on)}		4.8	_	ns		
Turn-On Rise Time (Note 12)	tr	_	4.6	_	ns	$V_{DD} = 30V, V_{GS} = 10V$	
Turn-Off Delay Time (Note 12)	t _{D(off)}	_	32.5	_	ns	$I_D = 1A, R_G \cong 6.0\Omega$	
Turn-Off Fall Time (Note 12)	t _f	_	14.5	_	ns	7	

10. Measured under pulsed conditions. Pulse width \leq 300µs; duty cycle \leq 2%. 11. For design aid only, not subject to production testing. 12. Switching characteristics are independent of operating junction temperatures.

Notes:

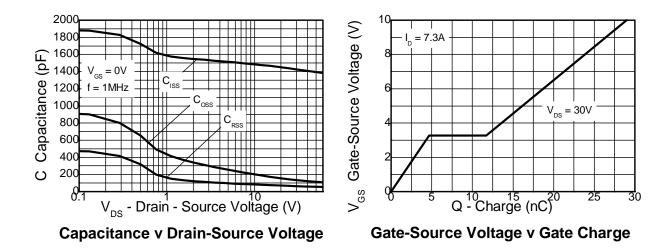


Typical Characteristics

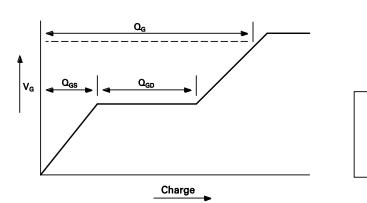




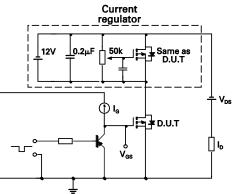
Typical Characteristics (cont.)



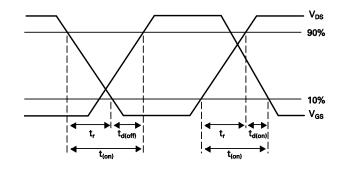
Test Circuits



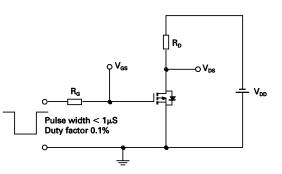
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms

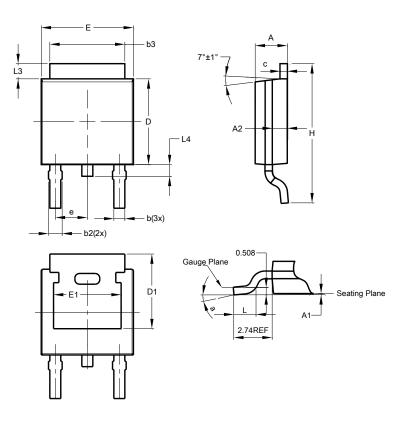


Switching time test circuit



Package Outline Dimensions

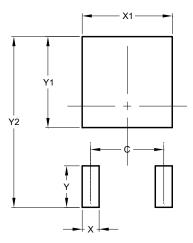
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



TO252 (DPAK)					
Dim	Min	Max	́Тур		
Α	2.19	2.39	2.29		
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Ε	6.45	6.70	6.58		
E1	4.32	-	-		
Н	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	4.572
Х	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700



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